



12-22-05

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/677,005
Applicant: Jer-shen Maa *et al.*
Filed: September 30, 2003
Group #: 1763
Examiner: George A. Goudreau

Confirmation Number: 7276

Docket No: SLA.0780
Customer No: 55376
For: Method of Making Relaxed Silicon-Germanium on Insulator via Layer Transfer with Stress Reduction

MS AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

RESPONSE TO OFFICE ACTION UNDER 37 C.F.R. § 1.111
Change of Correspondence Address
Introductory Comments

In response to the Office Action dated October 4, 2005, please amend the above-identified Application as follows:

Amendment to the Specification None

Amendment to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Amendment to the Drawings None

Remarks/Arguments begin on page 8 of this paper.

An **Appendix** is not included.